

GENERAL DESCRIPTION

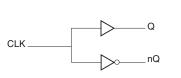
The 8302-01 is a low skew, 1-to-2 LVCMOS/LVTTL Fanout Buffer w/Complementary Output. The 8302-01 has a single ended clock input. The single ended clock input accepts LVCMOS or LVTTL input levels. The 8302-01 is characterizedat full 3.3V for input V_{DD} , and mixed 3.3V and 2.5V foroutput operating supply modes (V_{DDO}). Guaranteed output and partto-part skew characteristics make the 8302-01 ideal for clock distribution applications demanding well defined performance and repeatability.

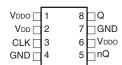
FEATURES

- Complementary LVCMOS / LVTTL output
- LVCMOS / LVTTL clock input accepts LVCMOS or LVTTL input levels
- Maximum output frequency: 250MHz
- Output skew: 165ps (maximum)
- Part-to-part skew: 800ps (maximum)
- · Small 8 lead SOIC package saves board space
- Full 3.3V or 3.3V core, 2.5V supply modes
- 0°C to 70°C ambient operating temperature
- · Industrial temperature information available upon request

BLOCK DIAGRAM

PIN ASSIGNMENT





8302-01 8-Lead SOIC 3.8mm x 4.8mm, x 1.47mm package body M Package Top View

TABLE 1. PIN DESCRIPTIONS

Number	Name	Ту	уре	Description
1, 6	V _{DDO}	Power		Output supply pins.
2	V _{DD}	Power		Core supply pin.
3	CLK	Input	Pulldown	LVCMOS / LVTTL clock input.
4,7	GND	Power		Power supply ground.
5	nQ	Output		Complementary clock output. LVCMOS / LVTTL interface levels.
8	Q	Output		Clock output. LVCMOS / LVTTL interface levels.

NOTE: Pullup and Pulldown refer to internal input resistors. See Table 2, Pin Characteristics, for typical values.

TABLE 2. PIN CHARACTERISTICS

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C _{IN}	Input Capacitance				4	pF
	Power Dissipation Capacitance	$V_{DD}, V_{DDO} = 3.465V$		22		pF
C _{PD}	(per output)	$V_{DD} = 3.465$ V, $V_{DDO} = 2.625$ V		16		pF
R _{PULLUP}	Input Pullup Resistor			51		KΩ
R _{PULLDOWN}	Input Pulldown Resistor			51		KΩ
R _{out}	Output Impedance			7		Ω

ABSOLUTE MAXIMUM RATINGS

Supply Voltage, V _{DD}	4.6V
Inputs, V _I	-0.5V to $V_{_{\rm DD}}$ + 0.5 V
Outputs, V _o	-0.5V to V_{DDO} + 0.5V
Package Thermal Impedance, $\boldsymbol{\theta}_{_{JA}}$	112.7°C/W (0 lfpm)
Storage Temperature, T _{stg}	-65°C to 150°C

NOTE: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V _{DD}	Core Supply Voltage		3.135	3.3	3.465	V
V _{DDO}	Output Power Supply Voltage		3.135	3.3	3.465	V
I _{DD}	Power Supply Current				13	mA
I _{DDO}	Output Supply Current				4	mA

TABLE 3B. LVCMOS / LVTTL DC CHARACTERISTICS	, V _{DD}	_D = V _{DDO} = 3.3V±5%, TA = 0°C το 70°C
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Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V _{IH}	Input High Voltage			2		V _{DD} + 0.3	V
V _{IL}	Input Low Voltage			-0.3		1.3	V
I _{IH}	Input High Current	CLK	$V_{_{DD}} = V_{_{IN}} = 3.465V$			150	μA
I _{IL}	Input Low Current	CLK	$V_{DD} = 3.465 V, V_{IN} = 0 V$	-5			μA
V	Output High Voltage		50 Ω to V _{DDO} /2	2.6			V
V _{OH}		;	I _{OH} = -100μA	2.9			V
V			50 Ω to V _{DDO} /2			0.5	V
V _{OL}	Output Low Voltage		Ι _{οL} = 100μΑ			0.2	V

TABLE 4A. AC CHARACTERISTICS, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, TA = 0°C to 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f _{MAX}	Output Frequency				250	MHz
tp _{LH}	Propagation Delay, Low-to-High; NOTE 1		1.8	2.18	2.7	ns
tsk(o)	Output Skew; NOTE 2, 4			50	165	ps
tsk(pp)	Part-to-Part Skew; NOTE 3, 4				800	ps
t _R / t _F	Output Rise/Fall Time	20% to 80%	300		800	ps
odc	Output Duty Cycle	<i>f</i> ≤133MHz	45		55	%
ouc		133MHz < <i>f</i> ≤ 250MHz	40		60	%

NOTE 1: Measured from $V_{\rm DD}/2$ of the input to $V_{\rm DDO}/2$ of the output.

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at $V_{DDO}/2$.

NOTE 3: Defined as skew between outputs on different devices operating at the same supply voltages

and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at $V_{_{DDO}}/2$.

NOTE 4: This parameter is defined in accordance with JEDEC Standard 65.

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V _{DD}	Positive Supply Voltage		3.135	3.3	3.465	V
V _{DDO}	Output Supply Voltage		2.375	2.5	2.625	V
I _{DD}	Power Supply Current				13	mA
I _{DDO}	Output Supply Current				4	mA

Table 3C. Power Supply DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 2.5V \pm 5\%$, Ta = 0°C to 70°C to 7

TABLE 3D. LVCMOS / LVTTL DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 2.5V \pm 5\%$, TA = 0°C to 70°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V _{IH}	Input High Voltage			2		V _{DD} + 0.3	V
V _{IL}	Input Low Voltage			-0.3		1.3	V
I _{IH}	Input High Current	CLK	$V_{DD} = V_{IN} = 3.465V$			150	μA
I _{IL}	Input Low Current	CLK	$V_{_{DD}} = 3.465 \text{V}, V_{_{IN}} = 0 \text{V}$	-5			μA
V	Output High Voltage		50 Ω to V _{DDO} /2	1.8			V
V _{OH}			Ι _{ΟΗ} = -100μΑ	2.2			V
V			50 Ω to V _{DDO} /2			0.5	V
V _{ol}	Output Low Voltage		I _{OL} = 100μA			0.2	V

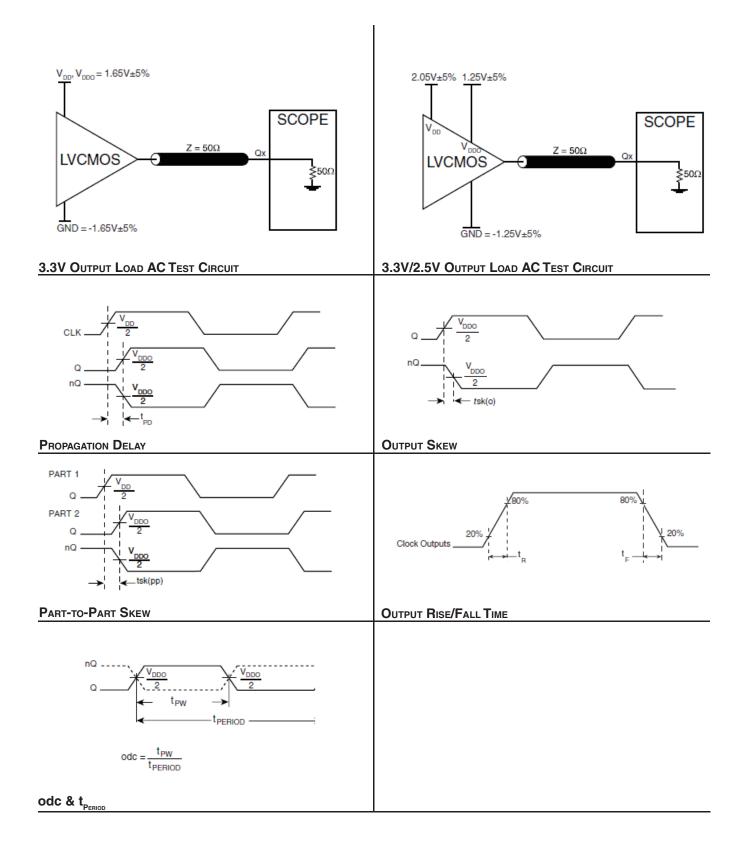
Table 4B. AC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 2.5V \pm 5\%$, Ta = 0°C to 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f _{MAX}	Output Frequency				250	MHz
tp _{LH}	Propagation Delay, Low-to-High; NOTE 1		1.9		2.9	ns
tsk(o)	Output Skew; NOTE 2, 4				250	ps
tsk(pp)	Part-to-Part Skew; NOTE 3, 4				900	ps
t _R / t _F	Output Rise/Fall Time	20% to 80%	250		650	ps
odc		<i>f</i> ≤133MHz	45		55	%
Juc	Output Duty Cycle	133MHz < <i>f</i> ≤ 250MHz	40		60	%

NOTE 1: Measured from $V_{_{DD}}/2$ of the input to $V_{_{DDO}}/2$ of the output. NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at V_{DDO}/2.

NOTE 3: Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at V_{DDO}/2.

NOTE 4: This parameter is defined in accordance with JEDEC Standard 65.



PARAMETER MEASUREMENT INFORMATION

RELIABILITY INFORMATION

TABLE 5. $\boldsymbol{\theta}_{JA} \text{vs.}$ Air Flow Table

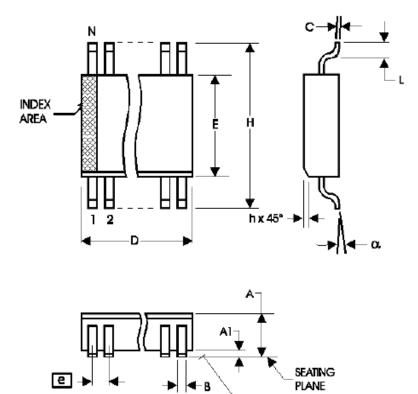
	0	200	500
ingle-Layer PCB, JEDEC Standard Test Boards	153.3°C/W	128.5°C/W	115.5°C/W
Iulti-Layer PCB, JEDEC Standard Test Boards	112.7°C/W	103.3°C/W	97.1°C/W

TRANSISTOR COUNT

The transistor count for 8302-01 is: 322



PACKAGE OUTLINE - SUFFIX M



.10 (.004)

TABLE 6. PACKAGE DIMENSIONS

CYMDOL	Millimeters		
SYMBOL	MINIMUN	MAXIMUM	
N	8		
А	1.35	1.75	
A1	0.10	0.25	
В	0.33	0.51	
С	0.19	0.25	
D	4.80	5.00	
E	3.80	4.00	
е	1.27 BASIC		
Н	5.80	6.20	
h	0.25	0.50	
L	0.40	1.27	
α	0°	8°	

Reference Document: JEDEC Publication 95, MS-012

TABLE 7. ORDERING INFORMATION

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
8302AM-01LF	8302A01L	8 lead SOIC	tube	0°C to 70°C
8302AM-01LFT	8302A01L	8 lead SOIC	tape and reel	0°C to 70°C

	REVISION HISTORY SHEET					
Rev	Table	Page	Description of Change	Date		
A	Τ7	8 10	Updated datasheet's header/footer with IDT from ICS. Removed ICS prefix from Part/Order Number column. Added Contact Page.	7/29/10		
A	Τ7	8	Ordering Information - updated part number to lead free and updated the order- ing information. Updated data sheet format.	11/17/15		
Α			Updated Header and Footer.	3/7/16		



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